METHOD AND APPARATUS FOR ELIMINATION OF TEOS/OZONE SILICON OXIDE SURFACE SENSITIVITY

ABSTRACT OF THE DISCLOSURE

A method and apparatus for reducing surface sensitivity of a $TEOS/O_3$ SACVD silicon oxide layer, formed over a substrate, that deposits a ramp layer while ramping pressure to a target deposition pressure and deposits an SACVD layer over the ramp layer. In one embodiment, the flow of ozone is stopped during the pressure ramp-up to control the thickness of the ramp layer.

Fig. 4